

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	11647	((257/300) or (257/295) or (257/296) or (257/303) or (257/306) or (257/E21.008) or (257/E21.012) or (257/E21.575)).CCLS.	US-PGPUB; USPAT	OR	OFF	2010/03/26 09:20
S1	1	("20050208728").PN.	US-PGPUB; USPAT	OR	OFF	2009/01/03 23:49
S2	1	("6297524").PN.	US-PGPUB; USPAT	OR	OFF	2009/01/03 23:49
S3	10516	((257/303) or (257/296) or (257/298) or (257/300) or (257/301) or (257/308) or (257/E21.012) or (257/E27.048) or (438/238) or (438/239) or (438/242) or (438/386) or (438/399)).CCLS.	US-PGPUB; USPAT	OR	OFF	2009/01/03 23:51
S4	3954	S3 and capacitance and cover\$3 and insulat\$3	US-PGPUB; USPAT	OR	ON	2009/01/03 23:52
S5	974	S3 and capacitance and cover\$3 and insulat\$3 and (side near wall)	US-PGPUB; USPAT	OR	ON	2009/01/03 23:53
S6	75	S3 and capacitance and cover\$3 and insulat\$3 and (side near wall) and damascene	US-PGPUB; USPAT	OR	ON	2009/01/03 23:53
S7	10434	((257/300) or (257/295) or (257/296) or (257/303) or (257/306) or (257/E21.008) or (257/E21.012) or (257/E21.575)).CCLS.	US-PGPUB; USPAT	OR	OFF	2009/01/04 12:02
S8	2606	internal capacitor	US-PGPUB; USPAT	NEAR	ON	2009/10/12 21:26
S9	1415	internal capacitor	US-PGPUB; USPAT	ADJ	ON	2009/10/12 21:26
S10	5037	internal (capacitor or capacitance)	US-PGPUB; USPAT	NEAR	ON	2009/10/12 21:27

S11	12	S10 and metallization near plane	US-PGPUB; USPAT	NEAR	ON	2009/10/12 21:27
S12	929	directly adj covered	US-PGPUB; USPAT	NEAR	ON	2009/10/12 22:07
S13	0	semicondcutor directly adj covered	US-PGPUB; USPAT	NEAR	ON	2009/10/12 22:07
S14	87	semiconductor same directly adj covered	US-PGPUB; USPAT	NEAR	ON	2009/10/12 22:07

EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	0	insulat\$ capacitance metallization plane substrate homogeneous cohesive elevation parallel patterning lattice	USPAT; UPAD	AND	ON	2010/03/26 09:22
L5	0	insulat\$ capacitance metallization plane substrate homogeneous cohesive elevation	USPAT; UPAD	AND	ON	2010/03/26 09:22
L6	3	insulat\$ capacitance plane substrate homogeneous cohesive elevation	USPAT; UPAD	AND	ON	2010/03/26 09:23

3/26/2010 9:28:33 AM**C:\Documents and Settings\tchui\My Documents\EAST\Workspaces\10512017.wsp**